

## Refine Search

09/927803

### Search Results -

Terms	Documents
L1 and (nonvolatile adj memory)	7

Database:

US Pre-Grant Publication Full-Text Database  
US Patents Full-Text Database  
US OCR Full-Text Database  
EPO Abstracts Database  
JPO Abstracts Database  
Derwent World Patents Index  
IBM Technical Disclosure Bulletins

Search:

L2

Refine Search

Recall Text

Clear

Interrupt

### Search History

DATE: Monday, December 29, 2003 [Printable Copy](#) [Create Case](#)

**Set Name Query**  
side by side

**Hit Count Set Name**  
result set

DB=USPT; PLUR=YES; OP=ADJ

<u>L2</u>	L1 and (nonvolatile adj memory)	7	<u>L2</u>
<u>L1</u>	DDD and LDD	205	<u>L1</u>

END OF SEARCH HISTORY

## Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 7 of 7 returned.

☐ 1. Document ID: US 6071775 A

L2: Entry 1 of 7

File: USPT

Jun 6, 2000

US-PAT-NO: 6071775

DOCUMENT-IDENTIFIER: US 6071775 A

TITLE: Methods for forming peripheral circuits including high voltage transistors with LDD structures.

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 2. Document ID: US 6051465 A

L2: Entry 2 of 7

File: USPT

Apr 18, 2000

US-PAT-NO: 6051465

DOCUMENT-IDENTIFIER: US 6051465 A

TITLE: Method for fabricating nonvolatile semiconductor memory device

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 3. Document ID: US 5917218 A

L2: Entry 3 of 7

File: USPT

Jun 29, 1999

US-PAT-NO: 5917218

DOCUMENT-IDENTIFIER: US 5917218 A

TITLE: Peripheral circuits including high voltage transistors with LDD structures for nonvolatile memories

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 4. Document ID: US 5696006 A

L2: Entry 4 of 7

File: USPT

Dec 9, 1997

US-PAT-NO: 5696006

DOCUMENT-IDENTIFIER: US 5696006 A

TITLE: Method of manufacturing Bi-MOS device

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 5. Document ID: US 5691556 A

L2: Entry 5 of 7

File: USPT

Nov 25, 1997

US-PAT-NO: 5691556

DOCUMENT-IDENTIFIER: US 5691556 A

TITLE: Step-up semiconductor integrated circuit and electronic equipment using the semiconductor integrated circuit

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 6. Document ID: US 5641696 A

L2: Entry 6 of 7

File: USPT

Jun 24, 1997

US-PAT-NO: 5641696

DOCUMENT-IDENTIFIER: US 5641696 A

TITLE: Method of forming diffusion layer and method of manufacturing nonvolatile semiconductor memory device

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 7. Document ID: US 5317179 A

L2: Entry 7 of 7

File: USPT

May 31, 1994

US-PAT-NO: 5317179

DOCUMENT-IDENTIFIER: US 5317179 A

TITLE: Non-volatile semiconductor memory cell

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L1 and (nonvolatile adj memory)	7

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## Refine Search

### Search Results -

Terms	Documents
L3 and overlaps	8

Database:

US Pre-Grant Publication Full-Text Database  
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Derwent World Patents Index  
IBM Technical Disclosure Bulletins

Search:

L4

Refine Search

Recall Text

Clear

Interrupt

### Search History

DATE: Monday, December 29, 2003 [Printable Copy](#) [Create Case](#)

#### Set Name Query

side by side

#### Hit Count Set Name

result set

DB=USPT; PLUR=YES; OP=ADJ

<u>L4</u>	L3 and overlaps	8	<u>L4</u>
<u>L3</u>	L1 and sacrificial	20	<u>L3</u>
<u>L2</u>	L1 and (nonvolatile adj memory)	7	<u>L2</u>
<u>L1</u>	DDD and LDD	205	<u>L1</u>

END OF SEARCH HISTORY

## Hit List

**Search Results - Record(s) 1 through 8 of 8 returned.**

☐ 1. Document ID: US 5949105 A

L4: Entry 1 of 8

File: USPT

Sep 7, 1999

US-PAT-NO: 5949105

DOCUMENT-IDENTIFIER: US 5949105 A

TITLE: Insulated-gate field-effect transistor structure and method

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 2. Document ID: US 5834352 A

L4: Entry 2 of 8

File: USPT

Nov 10, 1998

US-PAT-NO: 5834352

DOCUMENT-IDENTIFIER: US 5834352 A

TITLE: Methods of forming integrated circuits containing high and low voltage field effect transistors therein

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 3. Document ID: US 5716861 A

L4: Entry 3 of 8

File: USPT

Feb 10, 1998

US-PAT-NO: 5716861

DOCUMENT-IDENTIFIER: US 5716861 A

TITLE: Insulated-gate field-effect transistor structure and method

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 4. Document ID: US 5591652 A

L4: Entry 4 of 8

File: USPT

Jan 7, 1997

US-PAT-NO: 5591652

DOCUMENT-IDENTIFIER: US 5591652 A

TITLE: Method of manufacturing flash memory with inclined channel region

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw. De
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☐ 5. Document ID: US 5502321 A

L4: Entry 5 of 8

File: USPT

Mar 26, 1996

US-PAT-NO: 5502321

DOCUMENT-IDENTIFIER: US 5502321 A

TITLE: Flash memory having inclined channel

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw. De
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☐ 6. Document ID: US 5098866 A

L4: Entry 6 of 8

File: USPT

Mar 24, 1992

US-PAT-NO: 5098866

DOCUMENT-IDENTIFIER: US 5098866 A

TITLE: Method for reducing hot-electron-induced degradation of device characteristics

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw. De
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☐ 7. Document ID: US 4928156 A

L4: Entry 7 of 8

File: USPT

May 22, 1990

US-PAT-NO: 4928156

DOCUMENT-IDENTIFIER: US 4928156 A

TITLE: N-channel MOS transistors having source/drain regions with germanium

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw. De
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☐ 8. Document ID: US 4837173 A

L4: Entry 8 of 8

File: USPT

Jun 6, 1989

US-PAT-NO: 4837173

DOCUMENT-IDENTIFIER: US 4837173 A

TITLE: N-channel MOS transistors having source/drain regions with germanium

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw. De
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L3 and overlaps	8

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